

**AMENDMENTS TO THE CLAIMS:**

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

**LISTING OF CLAIMS:**

1. (Previously presented) A fabrication method of a semiconductor integrated circuit device comprising the steps of:

(a) forming a first insulative film of a single layer or a stacked layer over a surface of a semiconductor wafer;

(b) removing the first insulative film on an edge of the semiconductor wafer;

(c) patterning the first insulative film after the step (b), on a product-obtainable area and on a non-product-obtainable area of the semiconductor wafer;

(d) etching the semiconductor wafer by using the first insulative film as a mask after the step (c);

(e) forming a second insulative film over the semiconductor wafer including a portion over the first insulative film after the step (d);

(f) mechanically and chemically polishing a surface of the second insulative film, thereby planarizing the surface thereof; and

(g) removing the second insulative film on the edge of the semiconductor wafer.

2. (Original) A fabrication method of a semiconductor integrated circuit device according to claim 1, wherein the step (b) is conducted by polishing with a polishing means using a slurry or a grinding wheel.

3. (Original) A fabrication method of a semiconductor integrated circuit device according to claim 2, wherein the polishing means has plural polishing drums in which each of the plural polishing drums are in contact with the edge of the semiconductor wafer in a region different from each other and the angle of contact changes in accordance with the shape of the edge of the semiconductor wafer.

4-32. (Canceled).

33. (Previously presented) A fabrication method of a semiconductor integrated circuit device comprising the steps of:

- (a) forming a first insulative film of a single layer or a stacked layer on a surface of a semiconductor wafer;
- (b) patterning the first insulative film;
- (c) etching the semiconductor wafer by using the first insulative film as a mask after the step (b);
- (d) forming a second insulative film on the semiconductor wafer including a portion on the first insulative film after the step (c);
- (e) mechanically and chemically polishing a surface of the second insulative film, thereby planarizing the surface thereof; and
- (f) polishing the second insulative film on an edge of the semiconductor wafer with the first insulative film being a polishing end point after the step (e).

34. (Previously presented) A fabrication method of a semiconductor integrated circuit device according to claim 33, wherein the step (f) is conducted by polishing with a polishing means using a slurry or a grinding wheel.

35. (Previously presented) A fabrication method of a semiconductor integrated circuit device according to claim 34, wherein the polishing means has plural polishing drums, in which each of the plural polishing drums is in contact with the edge of the semiconductor wafer in a region different from each other and the angle of contact changes in accordance with the shape of the edge of the semiconductor wafer.

36. (Previously presented) A fabrication method of a semiconductor integrated circuit device comprising the steps of:

- (a) forming a first insulative film on a surface of a semiconductor wafer;
- (b) patterning the first insulative film on a product-obtainable area and on a non-product-obtainable area of the semiconductor wafer;
- (c) forming a first conductive film over the semiconductor wafer including a portion on the first insulative film after the step (b);
- (d) mechanically and chemically polishing the first conductive film with the surface of the first insulative film on the product-obtainable area of the semiconductor wafer being a polishing end point; and
- (e) removing the first conductive film on the edge of the semiconductor wafer after the step (d).

37. (Previously presented) A fabrication method of a semiconductor integrated circuit device according to claim 36, wherein the step (e) is conducted by polishing with a polishing means using a slurry or a grinding wheel.

38. (Previously presented) A fabrication method of a semiconductor integrated circuit device according to claim 37, wherein the polishing means has plural polishing drums, in which each of the plural polishing drums is in contact with the edge of the semiconductor wafer in a region different from each other and the angle of contact changes in accordance with the shape of the edge of the semiconductor wafer.

39. (Previously presented) A fabrication method of a semiconductor integrated circuit device according to claim 36, wherein the first insulative film on the edge of the wafer is also removed by a predetermined thickness in the step (e) in a case where the first conductive film is a copper film or a copper alloy film.

40. (Previously presented) A fabrication method of a semiconductor integrated circuit device comprising the steps of:

- (a) forming a first conductive film on a semiconductor wafer;
- (b) patterning the first conductive film on a product-obtainable area and on a non-product-obtainable area of the semiconductor wafer, thereby forming first wirings;
- (c) forming a first insulative film over the semiconductor wafer including a portion on the first wirings;
- (d) mechanically and chemically polishing a surface of the first insulative film, thereby planarizing the surface thereof; and
- (e) removing the first insulative film on the edge of the semiconductor wafer after the step (d).

41. (Previously presented) A fabrication method of a semiconductor integrated circuit device according to claim 40, wherein the step (e) conducts polishing by a polishing means using a slurry or an abrasive wheel.

42. (Previously presented) A fabrication method of a semiconductor integrated circuit device according to claim 41, wherein the polishing means includes plural polishing drums, each of the plural polishing drums being in contact with the edge of the semiconductor wafer at a region different from each other and the angle of contact thereof changes depending on the shape of the edge of the semiconductor wafer.

43. (Previously presented) A fabrication method of a semiconductor integrated circuit device comprising the steps of:

(a) forming a single layer or stacked layer of a first insulative film on a surface of a semiconductor wafer;

(b) removing the first insulative film on an edge of the semiconductor wafer;

(c) patterning the first insulative film on a product-obtainable area and on a non-product-obtainable area of the semiconductor wafer after the step (b);

(d) etching the semiconductor wafer by using the first insulative film as a mask after the step (c);

(e) forming a second insulative film over the semiconductor wafer including a portion on the first insulative film after the step (d);

(f) mechanically and chemically polishing a surface of the second insulative film, thereby planarizing the surface thereof;

- (g) forming a third insulative film over the semiconductor wafer after the step (f);
- (h) mechanically and chemically polishing the surface of the third insulative film, thereby planarizing the surface thereof; and
- (i) removing the third insulative film on the edge of the semiconductor wafer after the step (h).

44. (Previously presented) A fabrication method of a semiconductor integrated circuit device comprising the steps of:

- (a) forming a single layer or a stacked layer of a first insulative film on a surface of a semiconductor wafer;
- (b) patterning the first insulative film on a product-obtainable area and on a non-product-obtainable area of the semiconductor wafer;
- (c) etching the semiconductor wafer by using the first insulative film as a mask after the step (b);
- (d) forming a second insulative film over the semiconductor wafer including a portion on the first insulative film after the step (c);
- (e) mechanically and chemically polishing a surface of the second insulative film, thereby planarizing the surface thereof;
- (f) polishing the second insulative film on the edge of the semiconductor wafer with the first insulative film being a polishing end point after the step (e);
- (g) forming a third insulative film over the semiconductor wafer after the step (f);
- (h) mechanically and chemically polishing a surface of the third insulative film, thereby planarizing the surface thereof; and

(i) removing the third insulative film on an edge of the semiconductor wafer  
after the step (h).

45 and 46 (Canceled).